2SC4902

Silicon NPN Epitaxial

HITACHI

Application

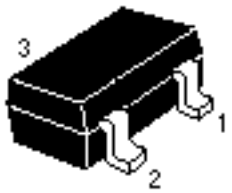
VHF / UHF wide band amplifier

Features

- High gain bandwidth product
  f_T = 6 GHz Typ
- High gain, low noise figure
  PG = 12.0 dB Typ, NF = 1.6 dB Typ at f = 900 MHz

Outline

MPAK



1. Emitter
2. Base
3. Collector

Hitachi semiconductor

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	20	V
Collector to emitter voltage	V_{CEO}	12	V
Emitter to base voltage	V_{EBO}	2	V
Collector current	I_C	30	mA
Collector power dissipation	P_C	150	mW
Junction temperature	Tj	150	°C
Storage temperature	Tstg	–55 to +150	°C

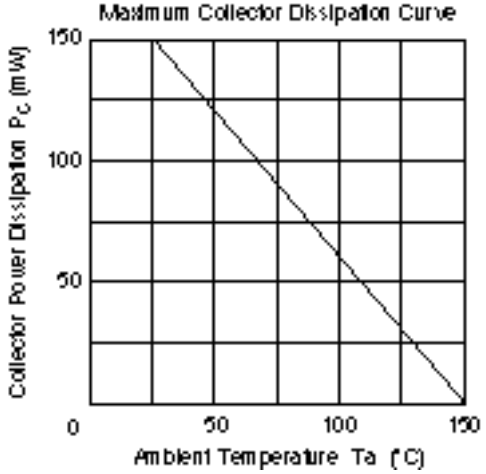
Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector cutoff current	I_{CBO}	—	—	10	µA	V_{CB} = 20 V, I_E = 0
	I_{CEO}	—	—	1	mA	V_{CE} = 12 V, R_{BE} = ∞
Emitter cutoff current	I_{EBO}	—	—	10	µA	V_{EB} = 2 V, I_C = 0
DC current transfer ratio	h_{FE}	50	120	250		V_{CE} = 5 V, I_C = 10 mA
Collector output capacitance	Cob	—	0.6	1.0	pF	V_{CB} = 5 V, I_E = 0, f = 1MHz
Gain bandwidth product	f_T	4.0	6.0	—	GHz	V_{CE} = 5 V, I_C = 10 mA
Power gain	PG	9.5	12.0	—	dB	V_{CE} = 5 V, I_C = 10 mA, f = 900 MHz
Noise figure	NF	—	1.6	3.0	dB	V_{CE} = 5 V, I_C = 5 mA, f = 900 MHz

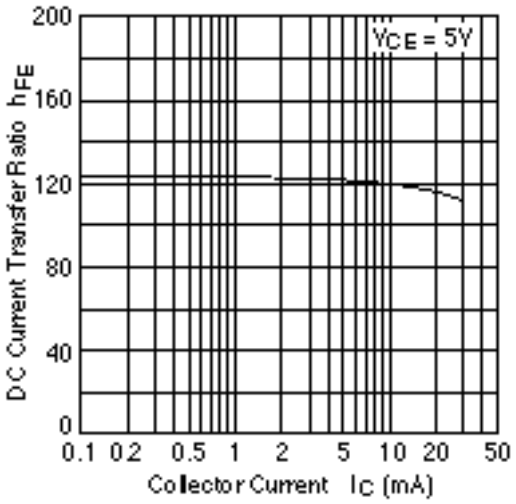
Note: Marking is “YL–”.

Attention: This is electrostatic sensitive device.

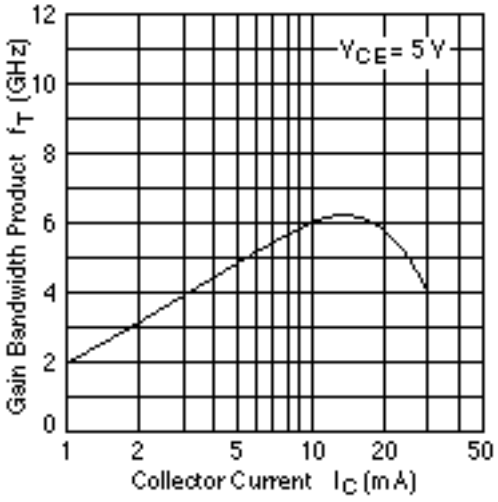
Maximum Collector Dissipation Curve



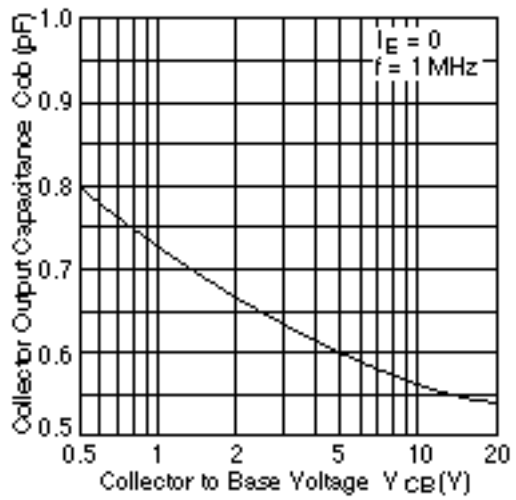
DC Current Transfer Ratio vs. Collector Current



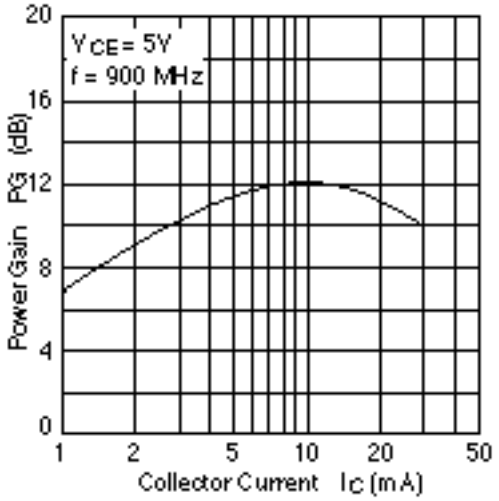
Gain Bandwidth Product vs. Collector Current



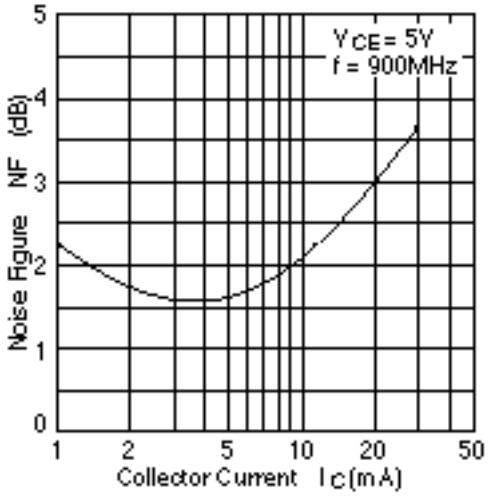
Collector Output Capacitance vs. Collector to Base Voltage



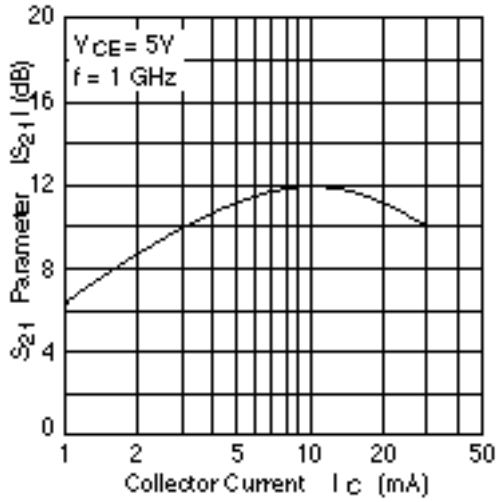
Power Gain vs. Collector Current



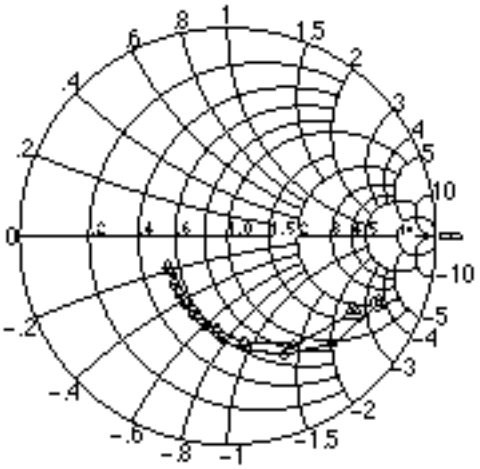
Noise Figure vs. Collector Current



S21 Parameter vs. Collector Current



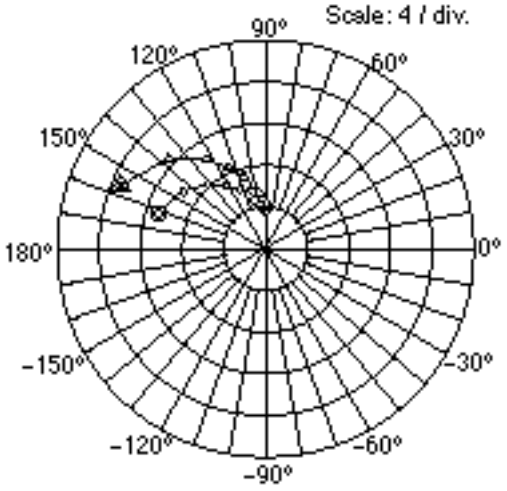
S11 Parameter vs. Frequency



Condition: V_{CE} = 5 V , Zo = 50 Ω
100 to 1000 (100 MHz step)
(Ic = 5 mA)
(Ic = 10 mA)

S21 Parameter vs. Frequency

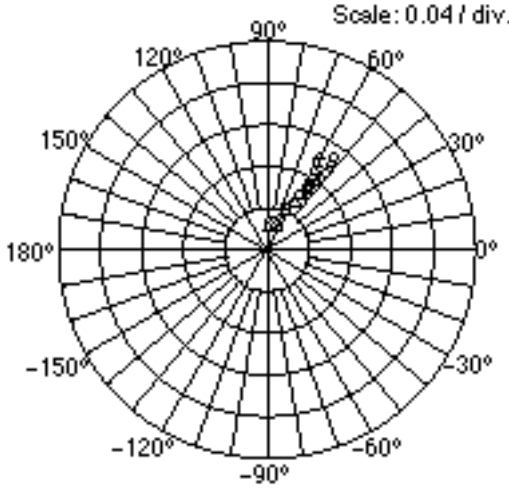
Scale: 4 / div.



Condition: V_{CE} = 5 V , Zo = 50 Ω
100 to 1000 (100 MHz step)
(Ic = 5 mA)
(Ic = 10 mA)

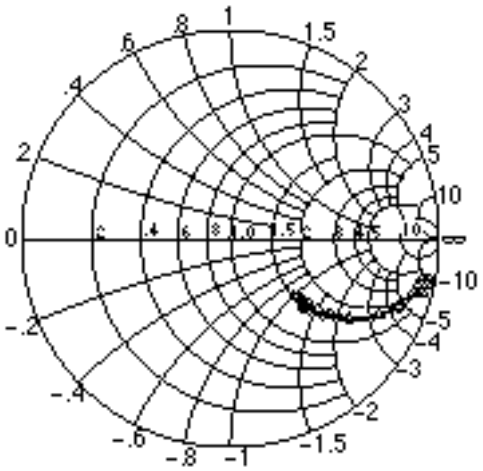
S12 Parameter vs. Frequency

Scale: 0.04 / div.



Condition: V_{CE} = 5 V , Zo = 50 Ω
100 to 1000 (100 MHz step)
(Ic = 5 mA)
(Ic = 10 mA)

S22 Parameter vs. Frequency



Condition: V_{CE} = 5 V , Zo = 50 Ω
100 to 1000 (100 MHz step)
(Ic = 5 mA)
(Ic = 10 mA)

S Parameter (V_{CE} = 5 V, I_C = 5 mA, Z_O = 50 Ω, Emitter common)

Freq.	S11		S21		S12		S22	
(MHz)	MAG.	ANG.	MAG.	ANG.	MAG.	ANG.	MAG.	ANG.
100	0.792	–23.8	10.79	161.8	0.0247	77.8	0.961	–12.2
200	0.721	–45.5	9.63	145.3	0.0455	67.4	0.876	–22.4
300	0.629	–64.5	8.31	131.9	0.0613	60.4	0.778	–29.6
400	0.556	–79.9	7.15	122.0	0.0717	56.2	0.695	–34.4
500	0.500	–93.1	6.18	113.9	0.0800	53.9	0.631	–37.3
600	0.448	–104.3	5.39	107.6	0.0869	52.7	0.581	–39.5
700	0.415	–113.7	4.77	102.2	0.0930	52.3	0.543	–40.9
800	0.388	–122.0	4.30	97.6	0.0989	52.5	0.514	–42.1
900	0.366	–130.5	3.89	93.1	0.104	53.4	0.491	–42.9
1000	0.354	–138.4	3.56	89.6	0.110	54.1	0.474	–44.3

S Parameter (V_{CE} = 5 V, I_C = 10 mA, Z_O = 50 Ω, Emitter common)

Freq.	S11		S21		S12		S22	
(MHz)	MAG.	ANG.	MAG.	ANG.	MAG.	ANG.	MAG.	ANG.
100	0.706	–31.5	15.14	156.8	0.0230	75.7	0.933	–15.8
200	0.608	–58.8	12.67	137.4	0.0403	64.5	0.803	–27.3
300	0.516	–80.9	10.28	123.8	0.0525	59.2	0.684	–33.8
400	0.449	–96.5	8.48	114.5	0.0609	57.0	0.597	–37.1
500	0.407	–110.4	7.13	107.0	0.0678	56.5	0.536	–38.8
600	0.376	–121.5	6.13	101.5	0.0747	56.5	0.494	–39.9
700	0.352	–131.4	5.36	96.7	0.0815	57.9	0.463	–40.4
800	0.334	–139.5	4.77	92.7	0.0882	58.7	0.441	–41.1
900	0.325	–147.9	4.28	88.9	0.0953	59.9	0.424	–41.5
1000	0.320	–154.4	3.90	85.9	0.102	60.6	0.412	–42.3

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